Dual bus buffer/line driver; 3-state

Rev. 1 — 8 May 2013

1. General description

The 74LVC2G125-Q100 provides a dual non-inverting buffer/line driver with 3-state output. The output enable input (pin $n\overline{OE}$) controls the 3-state output. A HIGH-level at pin $n\overline{OE}$ causes the output to assume a high-impedance OFF-state. Schmitt trigger action at all inputs makes the circuit highly tolerant of slower input rise and fall times.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
 - JESD8-7 (1.65 V to 1.95 V)
 - JESD8-5 (2.3 V to 2.7 V)
 - JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- ± 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low-power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options



3. Ordering information

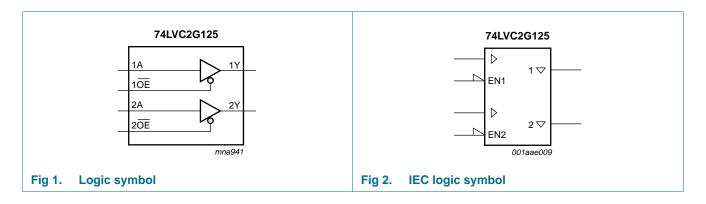
Table 1. Ordering inf	formation				
Type number Package					
	Temperature range	Name	Description	Version	
74LVC2G125DP-Q100	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2	
74LVC2G125DC-Q100	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1	

4. Marking

Table 2. Marking codes	
Type number	Marking code ^[1]
74LVC2G125DP-Q100	V25
74LVC2G125DC-Q100	V25

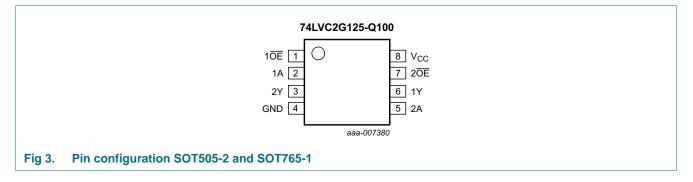
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
$1\overline{OE}, 2\overline{OE}$	1, 7	output enable input (active LOW)
1A, 2A	2, 5	data input
GND	4	ground (0 V)
1Y, 2Y	6, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table ^[1]		
Control	Input	Output
nOE	nA	nY
L	L	L
L	Н	Н
Н	Х	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground 0 V).

			0		,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+6.5	V
I _{OK}	output clamping current	$V_{O} > V_{CC}$ or $V_{O} < 0 V$	-	±50	mA
Vo	output voltage	Enable mode	<u>[1]</u> –0.5	V _{CC} + 0.5	V
		Disable mode	<u>[1]</u> –0.5	+6.5	V
		Power-down mode	<u>[1][2]</u> –0.5	+6.5	V
lo	output current	$V_{O} = 0 V \text{ to } V_{CC}$	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$	<u>[3]</u>	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When $V_{CC} = 0$ V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K. For XSON8, XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6.	Operating conditions				
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	V_{CC} = 1.65 V to 5.5 V; Enable mode	0	V _{CC}	V
		V_{CC} = 1.65 V to 5.5 V; Disable mode	0	5.5	V
		V _{CC} = 0 V; Power-down mode	0	5.5	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and	V_{CC} = 1.65 V to 2.7 V	-	20	ns/V
	fall rate	V _{CC} = 2.7 V to 5.5 V	-	10	ns/V

Dual bus buffer/line driver; 3-state

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
T _{amb} = -	40 °C to +85 °C					
VIH	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	$0.7V_{CC}$	-	-	V
VIL	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3V_{CC}$	V
√ _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 100 $\mu\text{A};$ V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		$I_0 = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	V
		I_{O} = 8 mA; V_{CC} = 2.3 V	-	-	0.3	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.4	V
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	V
		$I_0 = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_O = $-100~\mu\text{A};~V_{CC}$ = 1.65 V to 5.5 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -12$ mA; $V_{CC} = 2.7$ V	2.2	-	-	V
		$I_{O} = -24$ mA; $V_{CC} = 3.0$ V	2.3	-	-	V
		$I_O = -32$ mA; $V_{CC} = 4.5$ V	3.8	-	-	V
I	input leakage current	$V_{\rm I}$ = 5.5 V or GND; $V_{\rm CC}$ = 0 V to 5.5 V	-	±0.1	±5	μΑ
OZ	OFF-state output current	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{O} = 5.5 \text{ V or GND};$ $V_{CC} = 3.6 \text{ V}$	-	±0.1	±10	μA
OFF	power-off leakage current	$V_{I} \text{ or } V_{O} = 5.5 \text{ V}; V_{CC} = 0 \text{ V}$	-	±0.1	±10	μΑ
СС	supply current	$V_I = 5.5 V \text{ or GND};$ $V_{CC} = 1.65 V \text{ to } 5.5 V; I_O = 0 A$	-	0.1	10	μA
Alcc	additional supply current	per pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	5	500	μA
C _I	input capacitance		-	2	-	pF

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Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
T _{amb} = -	40 °C to +125 °C					
VIH	HIGH-level input voltage	V _{CC} = 1.65 V to 1.95 V	$0.65V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	2.0	-	-	V
		$V_{CC} = 4.5 V \text{ to } 5.5 V$	$0.7V_{CC}$	-	-	V
/ _{IL}	LOW-level input voltage	V _{CC} = 1.65 V to 1.95 V	-	-	$0.35V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7 V \text{ to } 3.6 V$	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	$0.3V_{CC}$	V
/ _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 100 μ A; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		$I_0 = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	V
		$I_0 = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.60	V
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V
		$I_0 = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V
/ _{он}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = -100 μ A; V_{CC} = 1.65 V to 5.5 V	$V_{CC}-0.1$	-	-	V
		$I_0 = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	0.95	-	-	V
		$I_0 = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.7	-	-	V
		$I_0 = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	1.9	-	-	V
		$I_0 = -24$ mA; $V_{CC} = 3.0$ V	2.0	-	-	V
		$I_0 = -32$ mA; $V_{CC} = 4.5$ V	3.4	-	-	V
	input leakage current	V_{I} = 5.5 V or GND; V_{CC} = 0 V to 5.5 V	-	-	±20	μA
OZ	OFF-state output current	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{O} = 5.5 \text{ V or GND};$ $V_{CC} = 3.6 \text{ V}$	-	-	±20	μA
OFF	power-off leakage current	V_{I} or V_{O} = 5.5 V; V_{CC} = 0 V	-	-	±20	μA
CC	supply current	$V_{I} = 5.5 V \text{ or GND};$ $V_{CC} = 1.65 V \text{ to } 5.5 V; I_{O} = 0 A$	-	-	40	μA
N _{CC}	additional supply current	per pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 2.3 V to 5.5 V	-	-	5	mA

Table 7. Static characteristics ... continued

[1] Typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

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11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground 0 V); for test circuit see Figure 6.

Symbol	Parameter	Conditions		-40	°C to +85	°C	–40 °C t	o +125 °C	Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
t _{pd}	propagation delay	nA to nY; see Figure 4	[2]						
		V_{CC} = 1.65 V to 1.95 V		1.0	3.7	9.1	1.0	11.4	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.5	4.8	0.5	6.0	ns
		$V_{CC} = 2.7 V$		1.0	2.7	4.8	1.0	6.0	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	2.3	4.3	0.5	5.5	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	1.9	3.7	0.5	4.6	ns
t _{en}	enable time	nOE to nY; see Figure 5	[3]						
		V_{CC} = 1.65 V to 1.95 V		1.5	4.3	9.9	1.5	12.4	ns
		V_{CC} = 2.3 V to 2.7 V		1.0	2.8	5.6	1.0	7.0	ns
		$V_{CC} = 2.7 V$		1.5	3.3	5.7	1.5	7.1	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	2.4	4.7	0.5	5.9	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	2.0	3.8	0.5	4.8	ns
t _{dis}	disable time	nOE to nY; see Figure 5	[4]						
		V_{CC} = 1.65 V to 1.95 V		1.0	3.5	11.6	1.0	14.1	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	1.8	5.8	0.5	7.6	ns
		$V_{CC} = 2.7 V$		1.0	2.7	4.8	1.0	6.2	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.7	4.6	1.0	5.9	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	1.8	3.4	0.5	4.6	ns
C _{PD}	power dissipation	per buffer; V_I = GND to V_{CC}	[5]						
	capacitance	output enabled		-	18	-	-	-	pF
		output disabled		-	5	-	-	-	pF

[1] Typical values are measured at nominal V_{CC} and at $T_{amb} = 25$ °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

- $[3] \quad t_{en} \text{ is the same as } t_{PZH} \text{ and } t_{PZL}.$
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W). $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

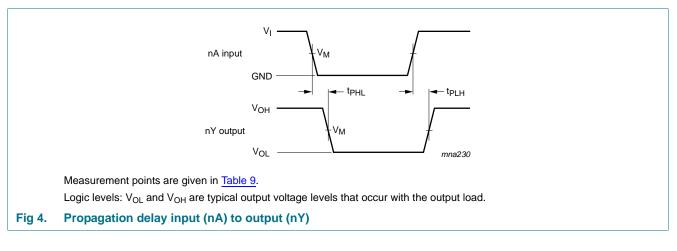
 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of outputs.

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12. Waveforms



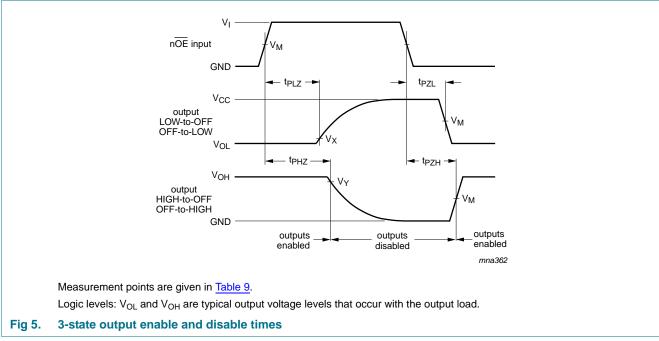


Table 9. Measurement points

Supply voltage	Input	Output		
V _{cc}	V _M	V _M	V _X	V _Y
1.65 V to 1.95 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
2.3 V to 2.7 V	$0.5V_{CC}$	0.5V _{CC}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
2.7 V	1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V
3.0 V to 3.6 V	1.5 V	1.5 V	V _{OL} + 0.3 V	$V_{OH} - 0.3 \ V$
4.5 V to 5.5 V	$0.5V_{CC}$	$0.5V_{CC}$	V _{OL} + 0.3 V	V _{OH} – 0.3 V

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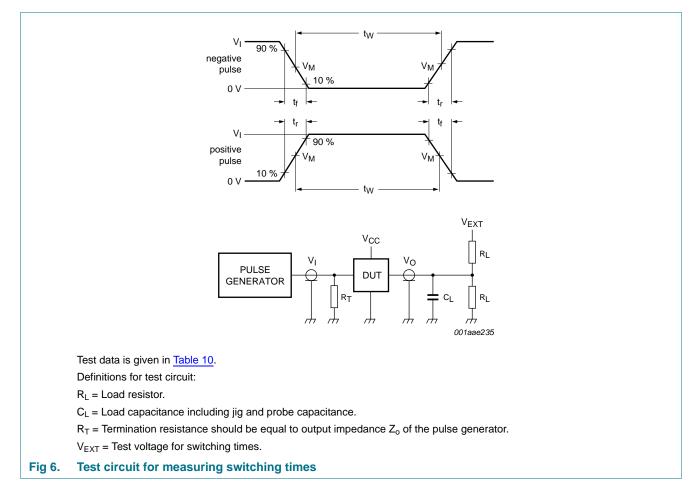


Table 10. Test data

Supply voltage	Input		Load		V _{EXT}		
V _{cc}	VI	t _r , t _f	CL	RL	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
1.65 V to 1.95 V	V _{CC}	\leq 2.0 ns	30 pF	1 kΩ	open	GND	$2V_{CC}$
2.3 V to 2.7 V	V _{CC}	\leq 2.0 ns	30 pF	500 Ω	open	GND	$2V_{CC}$
2.7 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open	GND	6 V
3.0 V to 3.6 V	2.7 V	\leq 2.5 ns	50 pF	500 Ω	open	GND	6 V
4.5 V to 5.5 V	V _{CC}	\leq 2.5 ns	50 pF	500 Ω	open	GND	$2V_{CC}$

13. Package outline

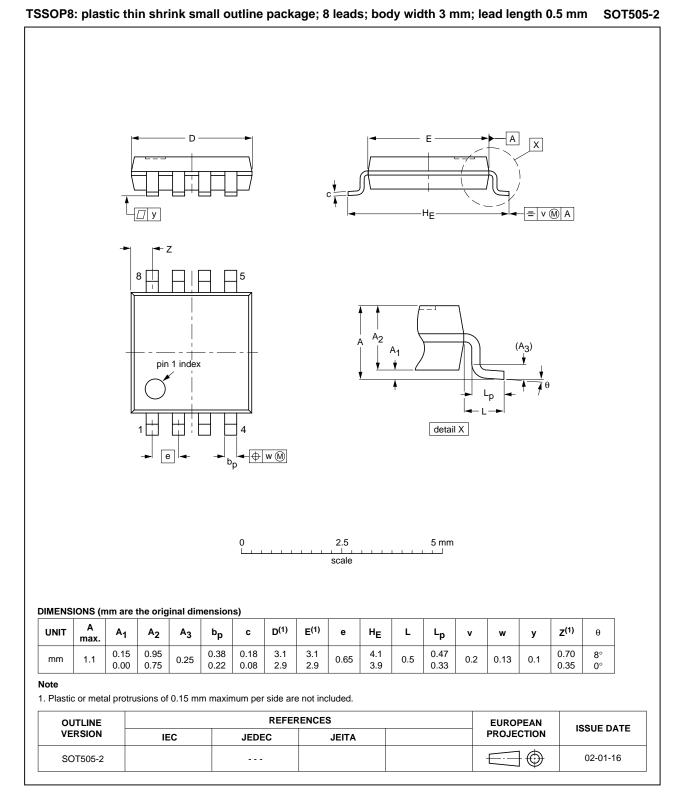


Fig 7. Package outline SOT505-2 (TSSOP8)

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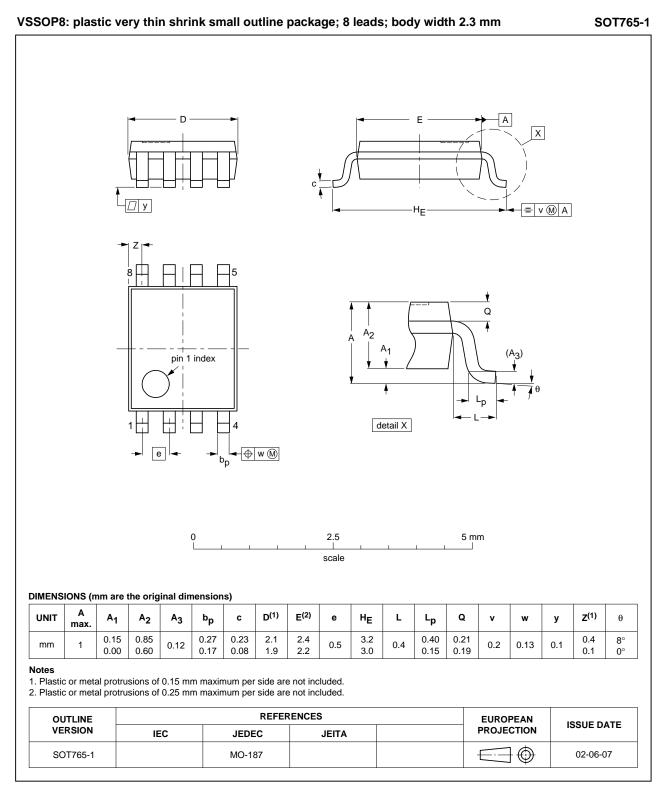


Fig 8. Package outline SOT765-1 (VSSOP8)

74LVC2G125_Q100

Product data sheet

14. Abbreviations

Acronym CMOS DUT	Description Complementary Metal-Oxide Semiconductor Device Under Test
	· · ·
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
74LVC2G125_Q100 v.1	20130508	Product data sheet	-	-	

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contact information

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Dual bus buffer/line driver; 3-state

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